Abstract:

Method for producing a semiconductor wafer with a profiled edge

The invention relates to a method for producing a semiconductor wafer with a profiled edge, comprising the following steps:
the separation of the semiconductor wafer from a crystal;
an edge profile producing step, in which the edge is mechanically machined and acquires a profile that is true to scale with respect to a target profile;
a mechanical machining step, in which a thickness of the semiconductor wafer is reduced; and
an edge profile machining step, in which the edge is mechanically machined and acquires the target profile.

Fig. 1